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Bekunftigung, â€¢ vollstÃ¤ndig kompatibel mit
Windows 7, and 64-bit..The present invention
relates to compound semiconductor junction
devices, and more particularly to producing a series
of junction devices from the same growth for batch
processing and reliability improvements. Silicon and
gallium arsenide diodes are known and have been
produced in a variety of configurations. Typically,
high p/n-type junction diode configurations have
been used to make a light-emitting device, such as
a light-emitting diode, including a series of such
diodes arranged in a string, or array. All of the
diodes in the array, however, are of the same type
(high or low p/n) and the array has a different
configuration or design for each type. That is, each
array is designed or configured for a specific
purpose. This is very time-consuming and laborious,
particularly when a large number of arrays are to be
produced. More recently, arrays of diode-type
devices have been made in silicon carbide of the

same type for a specific purpose. These devices may employ epitaxially-grown films of silicon carbide on a carbon-coated silicon carbide substrate. According to the present invention, a new junction diode array and growing method is provided which makes arrays of junction diode-type devices in silicon carbide of different types without the need to attach the different devices to one another. According to the present invention, a junction diode array is provided having a junction diode having a semi-insulating silicon carbide semiconductor substrate and an N-type region on the substrate, the diode also having an N-type region that is an epitaxial layer on the substrate and a P-type region on the epitaxial layer of the diode. The diode is characterized by the fact that a P-type region having a predetermined location on the epitaxial layer of the diode and a P-type region having a different location on the epitaxial layer of the diode are differently configured, and are made in a way to preclude the two regions from physically contacting. This same configuration is also achieved by doping the two different parts of the P-type region to make the parts of the P-type region of different configurations. Such a di c6a93da74d

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